

IN THE CLAIMS

Claims 1-18: Canceled.

19. (Previously Presented) A method of accomplishing chemical mechanical planarization of a Cu/Ta/TaN surface comprising:
- providing a single-step slurry solution including a combination selected from the group consisting of (i) H_2O_2 with H_3PO_4 , H_2SO_4 , HNO_3 , oxalic acid, acetic acid, or organic acid, (ii) HNO_3 with H_3PO_4 , or H_2SO_4 ; and (iii) an oxidizing reagent with HF;
- applying the solution to the surface; and
- planarizing both the Cu and at least one of the Ta and TaN during a single processing step.
20. (Previously Presented) The method of claim 19, wherein the slurry solution is selected from the group consisting of H_2O_2 with H_3PO_4 , H_2SO_4 , HNO_3 , oxalic acid, or organic acid.
21. (Previously Presented) The method of claim 19, wherein the slurry solution is selected from the group consisting of HNO_3 with H_3PO_4 , or H_2SO_4 .
22. (Previously Presented) The method of claim 19, wherein the slurry solution is selected from the group consisting of an oxidizing reagent with HF.
23. (Previously Presented) The method of claim 19, further including in the slurry solution an additive selected from the group consisting of selected from the group consisting of HCl, aliphatic alcohols, butylated hydroxytoluene, Agidol-2,2,6-di-tert-butyl-4[(dimethylamino)methyl]phenol, 2,6-di-tert-4N,N-dimethylaminomethylphenol, borax,

ethylene glycol, ZnSO_4 , methanol, propanol, poly(oxyethylene)lauryl ether, malic acid, $\text{HOOC}(\text{CX}_2)_n\text{COOH}$ wherein $\text{X}=\text{OH}$, amine, H and $n=1-4$), 3% tartaric acid, 1% ethylene glycol, 1,2,4-triazole, 1,2,3-triazole, tetrazole, nonionic surfactant, ethanol, trifluoroethanol, SiF_6 , organic salt surfactant, polyvinyl alcohol, diphenylsulfamic acid, sodium oxalate, bezotriazole, sodium lignosulfonate, glycol, gelatin carboxymethylcellulose, amines, heavy metal salts, salts of Cu and Ta, KCl , CuCl_2 , SnCl_2 , propylene glycol, 2-ethyl-hexylamine, copper carbonate, low molecular weight alcohols, glycols, phenols, aliphatic alcohols, polyvinylalcohols, anionic surfactants, cationic surfactants, fluorocarbon-based surfactants, nonionic surfactants having the properties of preferentially adhering to certain materials, modifying thereby the chemical reactivity where so adhered, polyvinyl alcohol solution stabilizers and species inhibiting spontaneous decomposition of oxidizing agents, wetting agents or mixtures thereof.

24. (Previously Presented) The method of claim 19, further including in the slurry solution at least one of CuCl , FeCl , and FeCl_3 , in the slurry solution.
25. (Previously Presented) The method of claim 19, further including in the slurry solution at least one of $\text{Cu}(\text{NO}_3)_2$, CuSO_4 , EDTA, FeNO_3 , KOH , $\text{K}_2\text{S}_2\text{O}_5$, $(\text{NH}_4)_2\text{S}_2\text{O}_8$, CuNH_4Cl_3 , NaOH , NaClO_3 , NaNO_3 , $\text{Na}_2\text{S}_2\text{O}_8$, NH_4F , or NH_4OH .
26. (Previously Presented) The method of claim 19, further including in the slurry solution at least one of a molybdenum salt and phenolsulfonic acid in the slurry solution.
27. (Previously Presented) The method of claim 19, further comprising including abrasive particles selected from the group consisting SiO_2 , Al_2O_3 metallic and solid elemental particles, polymer particles, oxides, carbides, fluorides, carbonates, borides, nitrides, hydroxides of Al, Ag, Au, Ca, Ce, Cr, Cu, Fe, Gd, Ge, La, In, Hf, Mn, Ng, Ni, Nd, Pb, Pt, P, Sb, Sc, Sn, Tb, Ti, Ta, Th, Y, W, Zn, Zr, or mixtures thereof.

28. (Currently Amended) The method of claim 19, wherein the step of planarizing removes the Cu and at least one of the ~~Ti and TiN~~ Ta and TaN with approximately 1:1 selectivity.
29. (Currently Amended) ~~The slurry solution of claim 1,~~ The method of claim 19, wherein the slurry solution comprising comprises H₂O₂.
30. (Currently Amended) ~~The slurry solution of claim 1,~~ The method of claim 19, wherein the slurry solution comprising comprises H₃PO₄.
31. (Currently Amended) ~~The slurry solution of claim 1,~~ The method of claim 19, wherein the slurry solution comprising comprises H₂SO₄.
32. (Currently Amended) ~~The slurry solution of claim 1,~~ The method of claim 19, wherein the slurry solution comprising comprises HNO₃.
33. (Currently Amended) ~~The slurry solution of claim 1,~~ The method of claim 19, wherein the slurry solution comprising comprises an organic acid.
34. (Previously Presented) A reagent mixture for polishing a surface comprising at least one metal having a high rate of diffusion and at least one barrier layer that is mechanically hard, the mixture comprising:
- a) an oxidizing reactant selected from the group consisting of H₂O₂, HNO₃ and mixtures thereof; and
 - b) a co-reactant is selected from the group consisting of H₃PO₄, H₂SO₄, HNO₃, oxalic acid, acetic acid, organic acids and mixtures thereof,
- wherein the reagent mixture achieves about a 1:1 removal selectivity between the at least one metal and the at least one barrier layer.
35. (Previously Presented) The reagent mixture of claim 34, further comprising abrasive

particles selected from the group consisting SiO₂, Al₂O₃ metallic and solid elemental particles, polymer particles, oxides, carbides, fluorides, carbonates, borides, nitrides, hydroxides of Al, Ag, Au, Ca, Ce, Cr, Cu, Fe, Gd, Ge, La, In, Hf, Mn, Ng, Ni, Nd, Pb, Pt, P, Sb, Sc, Sn, Tb, Ti, Ta, Th, Y, W, Zn, Zr or mixtures thereof.

36. (Previously Presented) The reagent mixture of claim 35, wherein said abrasive particles are coated.
37. (Previously Presented) The reagent mixture of claim 36, wherein said coating is a chemically active species.
38. (Previously Presented) The reagent mixture of claim 37, wherein said coating is CeO₂.
39. (Previously Presented) The reagent mixture of claim 35, wherein said particles are produced by the sol method.
40. (Previously Presented) The reagent mixture of claim 35, wherein said particles have a range of sizes from approximately 4 nanometers to approximately 5 micrometers.
41. (Previously Presented) The reagent mixture of claim 40, wherein said particles have a size less than approximately 5 micrometers.
42. (Previously Presented) The reagent mixture of claim 34, wherein the at least one metal comprises copper.
43. (Previously Presented) The reagent mixture of claim 34, wherein the at least one barrier layer comprises tantalum or tantalum nitride.